Shinji Nakagomi

List of Publications by Year
in descending order

32 papers	1,673 citations	516710 16 h-index	434195 31 g-index
32 all docs	32 docs citations	32 times ranked	1471 citing authors

#	Article	IF	Citations
1	Magnesium Diffusion from MgO Substrates in Solâ€“Gelâ€Derived NiO Epitaxial Films: Effects of Heat Treatment Temperature and Liâ€Doping. Physica Status Solidi (B): Basic Research, 2021, 258, 2100230.	1.5	2
2	Crystal Orientation of Cubic NiO Thin Films Formed on Monoclinic Î²â€Ga 2 O 3 Substrates. Physica Status Solidi (B): Basic Research, 2020, 257, 1900669.	1.5	9
3	Electrical Conductivity Studies in Solâ€“Gelâ€Derived Liâ€Doped NiO Epitaxial Thin Films. Physica Status Solidi (B): Basic Research, 2020, 257, 2000330.	1.5	5
4	Î²â€Ga₂O₃/pâ€Type 4Hâ€SiC Heterojunction Diodes and Applications to Deepâ€UV Photodiodes. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1700796.	1.8	24
5	Crystal orientation of monoclinic Î²-Ga2O3 thin films formed on cubic MgO substrates with a Î³-Ga2O3 interfacial layer. Journal of Crystal Growth, 2017, 479, 67-74.	1.5	15
6	Beta-Gallium Oxide/SiC Heterojunction Diodes with High Rectification Ratios. ECS Journal of Solid State Science and Technology, 2017, 6, Q3030-Q3035.	1.8	25
7	Crystal orientations of Î²â€Ga₂O₃ thin films formed on <i>c</i>â€plane GaN substrate. Physica Status Solidi (B): Basic Research, 2016, 253, 1217-1221.	1.5	11
8	All-oxide pâ€“n heterojunction diodes comprising p-type NiO and n-type Î²-Ga₂O₃. Applied Physics Express, 2016, 9, 091101.	2.4	137
9	The orientational relationship between monoclinic Î²-Ga2O3 and cubic NiO. Journal of Crystal Growth, 2016, 445, 73-77.	1.5	18
10	NiO films grown epitaxially on MgO substrates by solâ€“gel method. Thin Solid Films, 2016, 601, 76-79.	1.8	20
11	Crystal orientations of Î²â€Ga₂O₃ thin films formed on <i>n</i>â€plane sapphire substrates. Physica Status Solidi (B): Basic Research, 2015, 252, 2117-2122.	1.5	0
12	Crystal orientations of Î²â€Ga₂O₃ thin films formed on <i>m</i>â€plane and <i>r</i>â€plane sapphire substrates. Physica Status Solidi (B): Basic Research, 2015, 252, 612-620.	1.5	13
13	Deep ultraviolet photodiodes based on the Î²-Ga2O3/GaN heterojunction. Sensors and Actuators A: Physical, 2015, 232, 208-213.	4.1	83
14	Hydrogen gas sensor with self temperature compensation based on Î²-Ga2O3 thin film. Sensors and Actuators B: Chemical, 2013, 187, 413-419.	7.8	64
15	Cross-sectional TEM imaging of Î²-Ga₂ O₃ thin films formed on <i>c</i> -plane and <i>a</i> -plane sapphire substrates. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1738-1744.	1.8	21
16	Deep ultraviolet photodiodes based on Î²-Ga2O3/SiC heterojunction. Applied Physics Letters, 2013, 103, .	3.3	193
17	Cross-sectional TEM imaging of Î²-Ga2 O3 thin films formed on c -plane and a -plane sapphire substrates (Phys. Status Solidi A 9âˆ•2013). Physica Status Solidi (A) Applications and Materials Science, 2013, 210, .	1.8	10
18	Crystal orientation of Î²-Ga2O3 thin films formed on c-plane and a-plane sapphire substrate. Journal of Crystal Growth, 2012, 349, 12-18.	1.5	162

#	Article	IF	Citations
19	Solar-blind photodiodes composed of a Au Schottky contact and a Î²-Ga2O3 single crystal with a high resistivity cap layer. Applied Physics Letters, 2011, 98, .	3.3	129
20	Hydrogen Sensitive Schottky Diode Based on <i>Î²</i>-Ga₂O₃ Single Crystal. Sensor Letters, 2011, 9, 31-35.	0.4	11
21	Enhancement of responsivity in solar-blind Î²-Ga2O3 photodiodes with a Au Schottky contact fabricated on single crystal substrates by annealing. Applied Physics Letters, 2009, 94, .	3.3	217
22	Field effect hydrogen sensor device with simple structure based on GaN. Sensors and Actuators B: Chemical, 2009, 140, 79-85.	7.8	20
23	Sol-gel prepared Î²-Ga2O3 thin films for ultraviolet photodetectors. Applied Physics Letters, 2007, 90, 031912.	3.3	376
24	Field-effect hydrogen sensor device with floating gate exhibiting unique behavior. Sensors and Actuators B: Chemical, 2007, 125, 408-414.	7.8	6
25	Hydrogen sensing by NKN thin film with high dielectric constant and ferroelectric property. Sensors and Actuators B: Chemical, 2005, 108, 490-495.	7.8	3
26	Large Voltage Response of Novel Diode of Pt-TiO_x-SiC Structure to Hydrogen Gas. Electrochemistry, 2003, 71, 394-397.	1.4	7
27	Hydrogen Gas Response of Pt-thin SiO₂-SiC Schottky Diode in the Presence of Oxygen. Electrochemistry, 2002, 70, 174-177.	1.4	3
28	Hydrogen sensitive negative switching behavior in metal-oxide-semiconductor devices. Sensors and Actuators B: Chemical, 2001, 72, 108-114.	7.8	10
29	Effects of Ambient Gases on Current-Voltage Characteristics of Pt-GaN Schottky Diodes at High Temperatures. Japanese Journal of Applied Physics, 2001, 40, L663-L665.	1.5	17
30	Influence of carbon monoxide, water and oxygen on high temperature catalytic metalâ€“oxideâ€“silicon carbide structures. Sensors and Actuators B: Chemical, 1997, 45, 183-191.	7.8	59
31	Evaluation of hydrogen-sensitive switching device by capacitance-voltage method. Sensors and Actuators B: Chemical, 1996, 37, 157-162.	7.8	1
32	Hydrogen-Sensitive Property of Switching Device with a Pdâ€“Si Tunnel Metal Insulator Semiconductor Structure. Japanese Journal of Applied Physics, 1994, 33, 6136-6140.	1.5	2